

NPN RF POWER TRANSISTOR

DESCRIPTION:

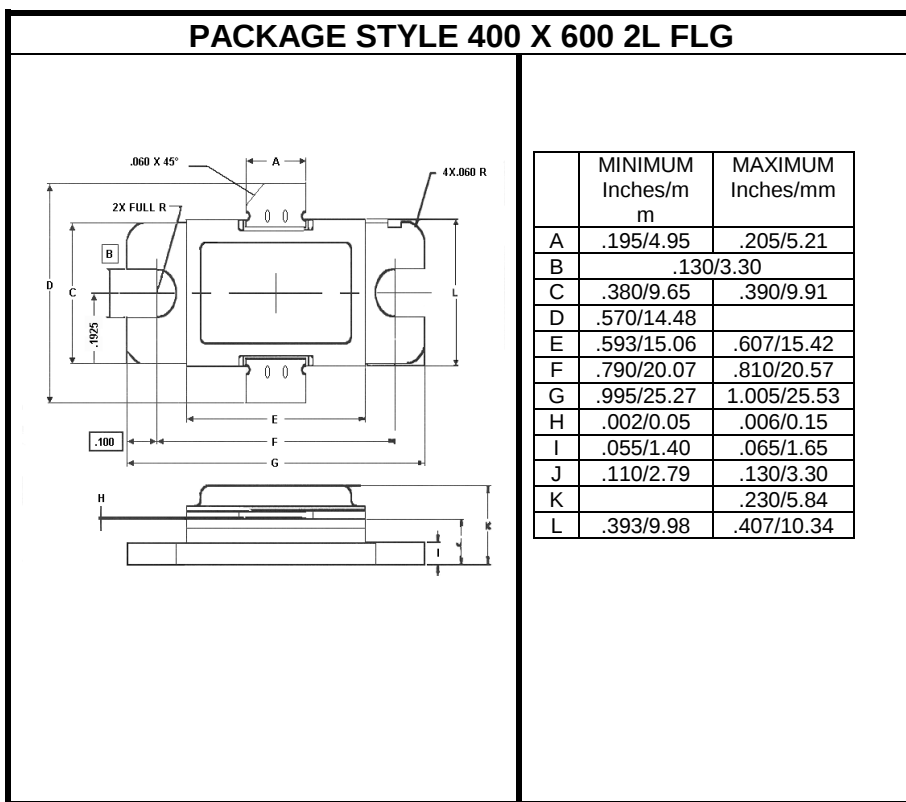
The **ASI AM1011-500** is a Common Base Device Designed for Pulsed L-Band Radar Amplifier Applications.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Hermetic Metal/Ceramic Package

MAXIMUM RATINGS

I_C	27 A
V_{CBO}	55 V
P_{DISS}	1360 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	0.11 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50\text{ mA}$	70			V
BV_{CES}	$I_C = 50\text{ mA}$	70			V
I_{CES}	$V_{CE} = 50\text{ V}$			40	mA
BV_{EBO}	$I_E = 30\text{ mA}$	3.0			V
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10		200	---
P_G	$V_{CE} = 50\text{ V}$ $P_{OUT} = 500\text{ W}$ $f = 1090\text{ MHz}$	8.5	8.5		dB
η_C	Pulse Width = 32 μS Duty Cycle = 2%	40	35		%